

DATA SHEET

Part No.	MN6627933
Package Code No.	LQFP100 - P - 1414

SEMICONDUCTOR COMPANY
MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD.

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MN6627933

Signal processing LSI for compact disc player

■ Overview

The MN6627933 is a signal processing LSI for CDs. It incorporates an optical servo (focus, tracking, and traverse servos) processing function, digital signal processing function (EFM demodulation and CIRC/CD-ROM error correction), digital servo processing function for spindle motor, anti-shock memory control function supporting 64M-bit, 16-Mbit, 4M-bit, or 1M-bit DRAM that enables compression/decompression for a disc rotation synchronous playback (i.e. jitter free), a decode function for MP3, Fs conversion processing function, a digital filter, and D/A converter. All the processing functions after the head amplifier (RF amplifier) are incorporated into a single chip.

This LSI includes Microsoft's technology and cannot be used and distributed without a license from Microsoft Corporation.

■ Features

(Optical Servo)

- Focus, tracking, and traverse servos
- Automatic adjustment functions
- (Focus / Tracking gain, Focus / Tracking offset, Focus / Tracking balance)
- Provided with a countermeasure for dropout
- Provided with an anti - shock detection function
- Provided with a track - cross function
- Drive output PWM drive function supported
- Provided with supply voltage monitoring and a servo gain automatic adjustment function

(Digital Signal Processing)

- Containing DSL and analog / digital PLL
- Provided with a frame synchronous detection / protection / interpolation
- Subcode data processing
 - Q-data CRC check
 - On-chip Q-data register
 - On-chip CD-TEXT data register
- CIRC error correction
 - C1 decoder : double error correction
 - C2 decoder : triple / quadruple error correction
 - On-chip deinterleaving 16K-RAM
- CD-ROM error correction
 - Q decoder : an error correction
 - P decoder : an error correction
 - Mode1 and Mode 2 compatible
- Audio data interpolation processing
 - 4 - sampling average value interpolation and previous value hold

(Spindle Motor Servo)

- CLV digital servo
- Servo gain setting function
- Shaft loss compensation setting function

(Audio Circuit)

- Soft muting
- Digital attenuation (2048 levels)
- Soft attenuation (2048 levels)
- Digital audio interface (EIAJ format)
- 8× oversampling digital filter
- On-chip low-voltage OP amp

(Audio Circuit) (continued)

- Bass boost filter, high-band notch filter, and surround function
- On-chip digital de-emphasis

(MP3 Decoding)

- Decoding of signals recorded in MPEG1 - layer3 or MPEG2 - layer3 format
- Decoding of signals recorded in MPEG1 - layer2 or MPEG2 - layer2 format
- Decoding of signals recorded in MPEG2.5 format
- Sampling rate conversion from signals recorded at $F_s = 32 \text{ kHz}$ or 48 kHz to 44.1 kHz

(SD Interface)

- Stream serial input from SD available

(Anti-shock Memory Controller)

- ADPCM 4-bit compression or expansion / decompression in full - bit (16 bits) mode
- External DRAM selectable

Async DRAM (Data bus width : 4 bits)

- 64M-bit DRAM $\times$ 1
- 16M-bit DRAM $\times$ 2
- 16M-bit DRAM $\times$ 1 + 4M-bit DRAM $\times$ 1
- 16M-bit DRAM $\times$ 1
- 4M-bit DRAM $\times$ 2
- 4M-bit DRAM $\times$ 1
- 1M-bit DRAM $\times$ 2
- 1M-bit DRAM $\times$ 1

Async DRAM (Data bus width : 16 bits)

- 128M-bit DRAM $\times$ 1
- 64M-bit DRAM $\times$ 1
- 16M-bit DRAM $\times$ 1
- 4M-bit DRAM $\times$ 1

SDRAM (Data bus width : 16 bits)

- 128M-bit DRAM $\times$ 1
- 64M-bit DRAM $\times$ 1
- 16M-bit DRAM $\times$ 1
- 4M-bit DRAM $\times$ 1

(Others)

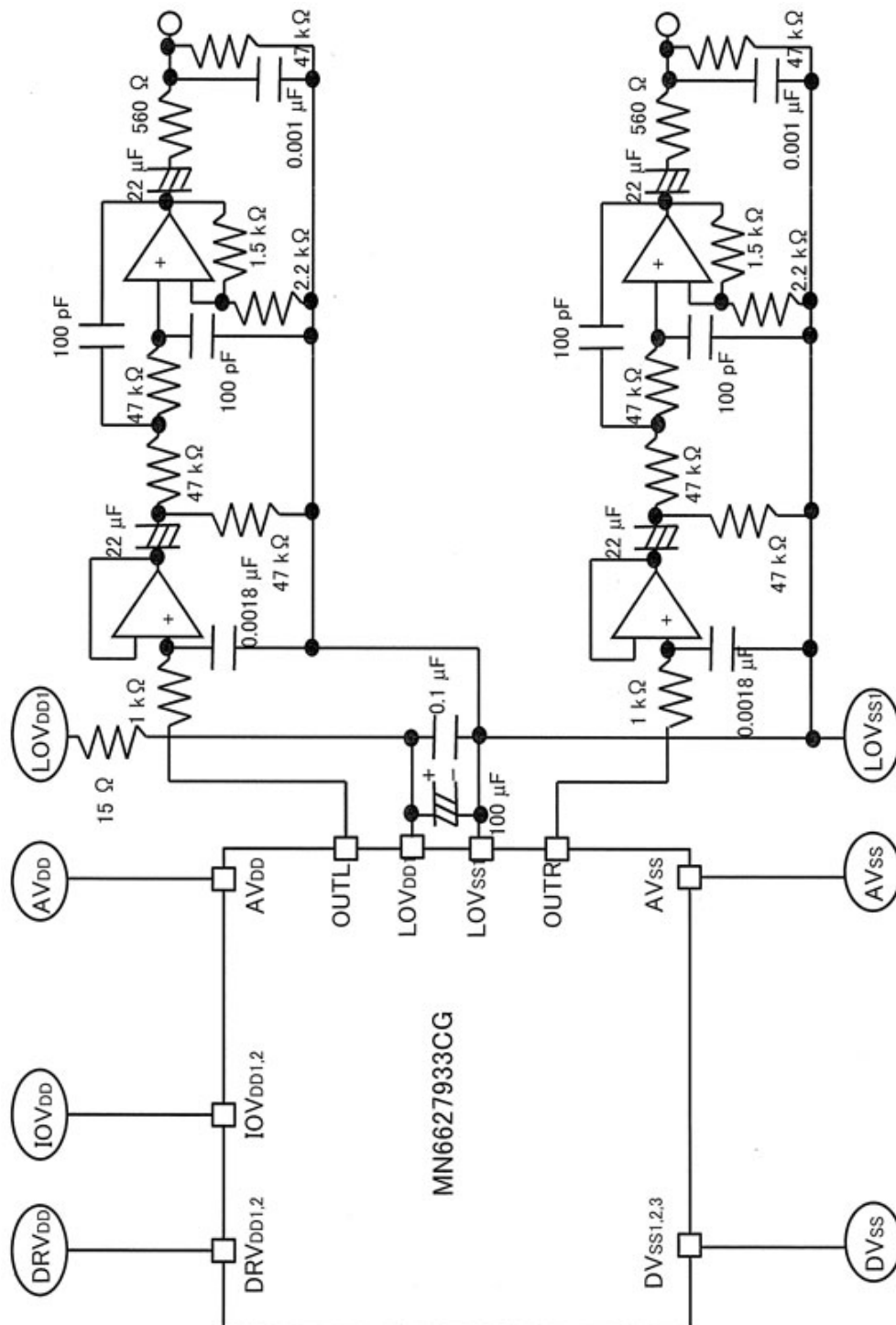
- Disc rotation mechanism has a synchronous playback (jitter-free) mode (-50% to $+50\%$)
- 8 $\times$ speed playback (when using jitter-free function)
- TX output (1 $\times$, 2 $\times$, 3 $\times$ and 4 $\times$ speed) supported
- Serial data output pitch shift function

A patent license must be acquired from the management company when using MPEG Layer3 products.

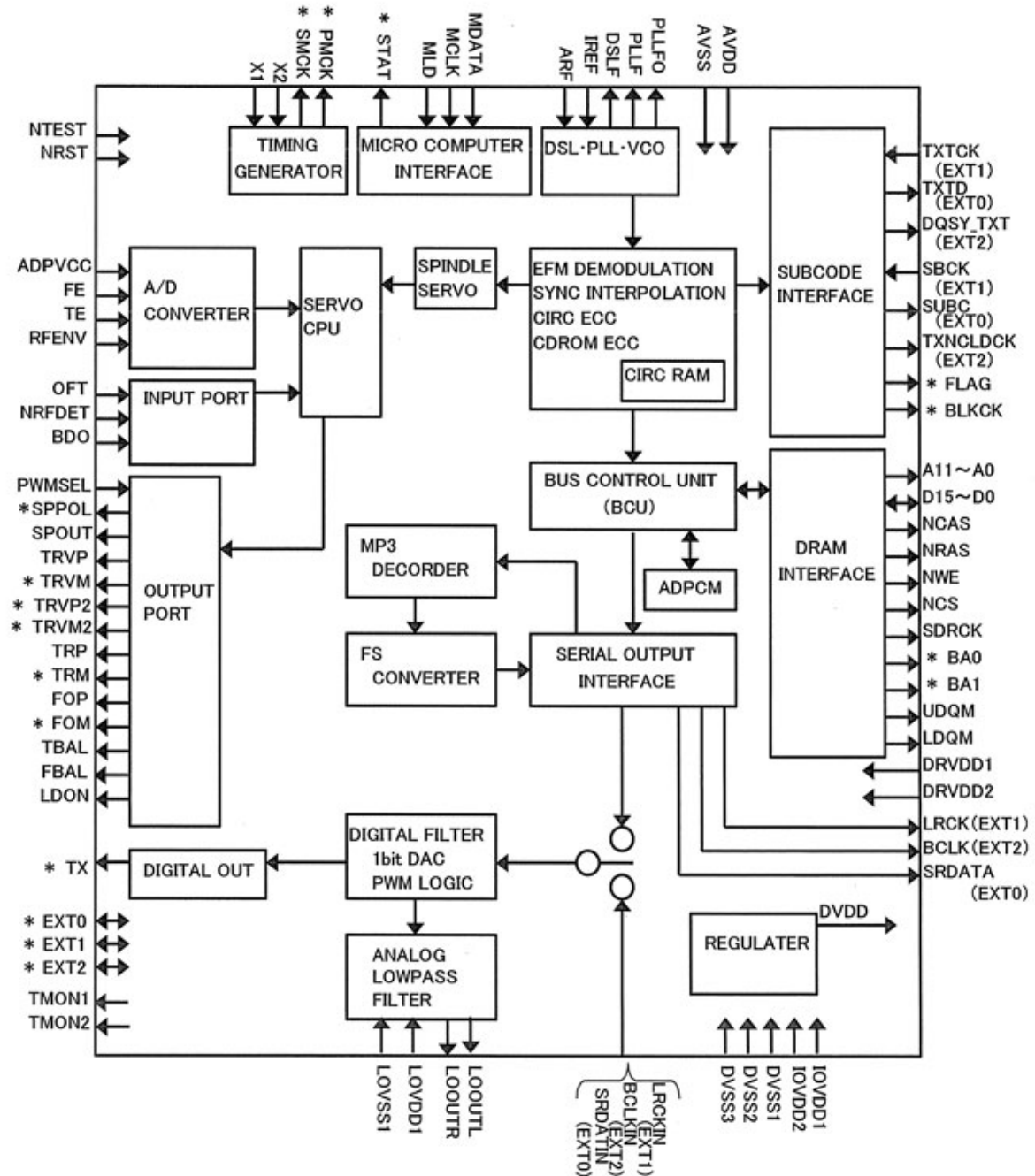
■ Applications

- Signal processing LSI for CDs (Compact Discs)

- Application Circuit
- DA Converter

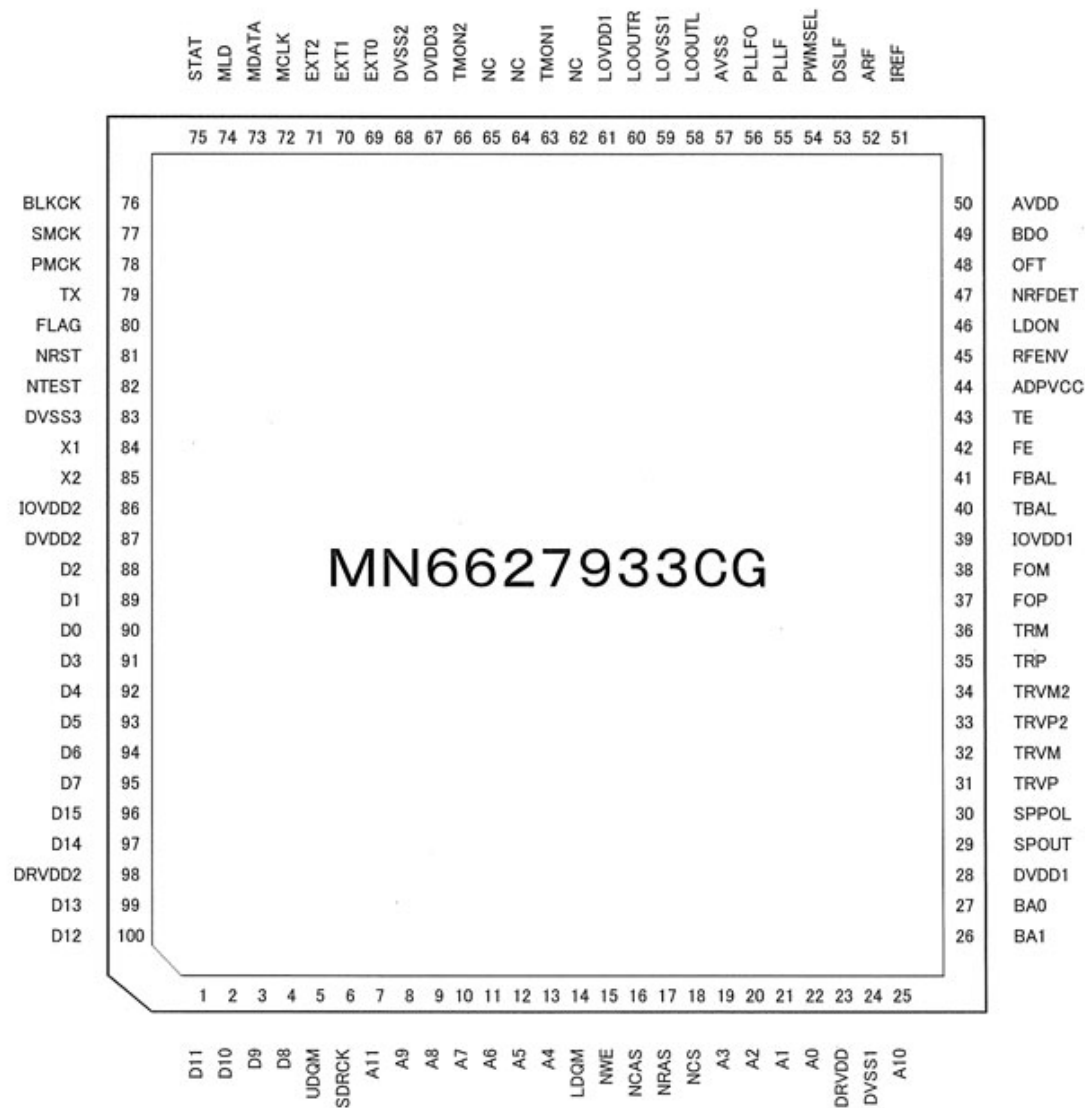


- Block Diagram
- DA Converter



■ Pin Assignments

100 - pin flat package (LQFP100 - P - 1414)



■ Pin Descriptions

Pin No.	Symbol	I/O	Function
1	D11	I/O	DRAM data signal I/O 11
2	D10	I/O	DRAM data signal I/O 10
3	D9	I/O	DRAM data signal I/O 9
4	D8	I/O	DRAM data signal I/O 8
5	UDQM	O	SDRAM upper byte data mask signal output
6	SDRCK	O	SDRAM clock signal output
7	A11	O	DRAM address signal output 11
8	A9	O	DRAM address signal output 9
9	A8	O	DRAM address signal output 8
10	A7	O	DRAM address signal output 7
11	A6	O	DRAM address signal output 6
12	A5	O	DRAM address signal output 5
13	A4	O	DRAM address signal output 4
14	LDQM	O	SDRAM lower byte data mask signal output
15	NWE	O	DRAM write enable signal output
16	NCAS	O	DRAM CAS control signal output
17	NRAS	O	DRAM RAS control signal output
18	NCS	O	SDRAM chip select signal output
19	A3	O	DRAM address signal output 3
20	A2	O	DRAM address signal output 2
21	A1	O	DRAM address signal output 1
22	A0	O	DRAM address signal output 0
23	DRVDD1	I	Power supply 1 for DRAM interface I/O
24	DVSS1	I	Ground 1 for digital circuits
25	A10	O	DRAM address signal output 10
26	*BA1	O	SDRAM bank selection signal output 1
27	*BA0	O	SDRAM bank selection signal output 0
28	DVDD1	I	Power supply 1 for internal digital circuits
29	SPOUT	O	Spindle drive signal output (absolute value)
30	*SPPOL	O	Spindle drive signal output (polarity)
31	TRVP	O	Traverse drive signal output (positive polarity)

Note) Pins marked with an asterisk can be switched to different signals by using microcontroller commands. The specifications of the DRAM pins depend on their type and capacitance.

■ Pin Descriptions (continued)

Pin No.	Symbol	I/O	Function
32	*TRVM	O	Traverse drive signal output (negative polarity)
33	*TRVP2	O	Traverse drive signal output 2 (positive polarity)
34	*TRVM2	O	Traverse drive signal output 2 (negative polarity)
35	TRP	O	Tracking drive signal output (positive polarity)
36	*TRM	O	Tracking drive signal output (negative polarity)
37	FOP	O	Focus drive signal output (positive polarity)
38	*FOM	O	Focus drive signal output (negative polarity)
39	IOVDD1	I	Power supply 1 for digital I/O
40	TBAL	O	Tracking balance adjustment signal output
41	FBAL	O	Focus balance adjustment signal output
42	FE	I	Focus error signal input
43	TE	I	Tracking error signal input
44	ADPVCC	I	Voltage input for supply voltage monitor
45	RFENV	I	RF envelope signal input
46	LDON	O	Laser ON signal output
47	NRFDET	I	RF detectioin signal input
48	OFT	I	Off - track signal input
49	BDO	I	Dropout signal input
50	AVDD	I	Power supply 1 for analog circuits
51	IREF	I	Analog reference current input
52	ARF	I	RF signal input
53	DSLFL	O	DSL loop filter pin
54	PWMSEL	I	PWM output mode selection input Low : Direct High : 3 – state
55	PLLFL	O	PLL loop filter pin (phase comparison output)
56	PLLFO	O	PLL loop filter pin (speed comparison output)
57	AVSS	I	Ground 1 for analog circuits
58	LOOUTL	O	L-ch audio output for line-out output
59	LOVSS1	I	Ground for line-out output
60	LOOUTR	O	R-ch audio output for line-out output
61	LOVDD1	I	Power supply for line-out output
62	N. C.	—	—
63	TMON1	O	Test monitor output 1

Note) Pins marked with an asterisk can be switched to different signals by using microcontroller commands.

■ Pin Descriptions (continued)

Pin No.	Symbol	I/O	Function
64	N. C.	—	—
65	N. C.	—	—
66	TMON2	O	Test monitor output 2
67	DVDD3	I	Power supply 3 for digital circuits
68	DVSS2	I	Ground 2 for digital circuits
69	*EXT0	I/O	Expansion I/O port 0
70	*EXT1	I/O	Expansion I/O port 1
71	*EXT2	I/O	Expansion I/O port 2
72	MCLK	I	Microcontroller command clock signal input
73	MDATA	I	Microcontroller command data signal input
74	MLD	I	Microcontroller command load signal input
75	*STAT	O	Status signal output
76	*BLKCK	O	Subcode block clock signal output
77	*SMCK	O	4.2336 MHz / 8.4672 MHz clock signal output
78	*PMCK	O	88.2 kHz clock signal output
79	*TX	O	Digital audio interface signal output
80	*FLAG	O	Flag signal output
81	NRST	I	LSI reset signal input
82	NTEST	I	Test mode setting input
83	DVSS3	I	Ground 3 for digital circuits
84	X1	I	Crystal oscillator circuit input
85	X2	O	Crystal oscillator circuit output
86	IOVDD2	I	Power supply 2 for digital I/O
87	DVDD2	I	Power supply 2 for internal digital circuits
88	D2	I/O	DRAM data signal I/O 2
89	D1	I/O	DRAM data signal I/O 1
90	D0	I/O	DRAM data signal I/O 0
91	D3	I/O	DRAM data signal I/O 3
92	D4	I/O	DRAM data signal I/O 4
93	D5	I/O	DRAM data signal I/O 5
94	D6	I/O	DRAM data signal I/O 6
95	D7	I/O	DRAM data signal I/O 7

Note) Pins marked with an asterisk can be switched to different signals by using microcontroller commands.

■ Pin Descriptions (continued)

Pin No.	Symbol	I/O	Function
96	D15	I/O	DRAM data signal I/O 15
97	D14	I/O	DRAM data signal I/O 14
98	DRVDD2	I	Power supply 2 for DRAM interface I/O
99	D13	I/O	DRAM data signal I/O 13
100	D12	I/O	DRAM data signal I/O 12

Note) Pins marked with an asterisk can be switched to different signals by using microcontroller commands. The specifications of the DRAM pins depend on their type and capacitance.

Note) If the MN6627932 and MN6627933 share the same PCB design, the followings are needed:

Pin 62 (N.C.): Low fixed

Pin 64 (N.C.): LOV_{DD2} applied

Pin 65 (N.C.): LOV_{SS2} applied

For details of the MN6627932, see the MN6627932 Product Standards and Specifications documents.

■ Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit	Note
A1	Supply voltage	$DRV_{DD1,2}$ $IOV_{DD1,2}$ AV_{DD} LOV_{DD1}	– 0.3 to + 4.6	V	$DV_{SS1,2,3} = 0\text{ V}$ $AV_{SS} = 0\text{ V}$ $LOV_{SS1} = 0\text{ V}$
A2	Input voltage	V_I	$DV_{SS1,2,3} - 0.3$ to $DRV_{DD1,2} + 0.3$ (Upper limit : 4.6 V) $DV_{SS1,2,3} - 0.3$ to $IOV_{DD1,2} + 0.3$ (Upper limit : 4.6 V) $AV_{SS} - 0.3$ to $AV_{DD} + 0.3$ (Upper limit : 4.6 V) $LOV_{SS1} - 0.3$ to $LOV_{DD1} + 0.3$ (Upper limit : 4.6 V)	V	$DV_{SS1,2,3} = 0\text{ V}$ $AV_{SS} = 0\text{ V}$ $LOV_{SS1} = 0\text{ V}$
A3	Output voltage	V_O	$DV_{SS1,2,3} - 0.3$ to $DRV_{DD1,2} + 0.3$ (Upper limit : 4.6 V) $DV_{SS1,2,3} - 0.3$ to $IOV_{DD1,2} + 0.3$ (Upper limit : 4.6 V) $AV_{SS} - 0.3$ to $AV_{DD} + 0.3$ (Upper limit : 4.6 V) $LOV_{SS1} - 0.3$ to $LOV_{DD1} + 0.3$ (Upper limit : 4.6 V)	V	$DV_{SS1,2,3} = 0\text{ V}$ $AV_{SS} = 0\text{ V}$ $LOV_{SS1} = 0\text{ V}$
A4	Power dissipation	P_D	560	mW	$DV_{SS1,2,3} = 0\text{ V}$ $AV_{SS} = 0\text{ V}$ $LOV_{SS1} = 0\text{ V}$
A5	Operating ambient temperature	T_{OPR}	– 30 to + 85	°C	
A6	Storage temperature	T_{STG}	– 50 to + 125	°C	

- Note) 1. The absolute maximum ratings are the limit values beyond which the IC may be broken. They do not assure operations.
2. Connect each of the DV_{SS1} , DV_{SS2} , DV_{SS3} , AV_{SS} , and LOV_{SS1} pins directly to ground and use at the same voltage.
 3. Connect each of the DRV_{DD1} , DRV_{DD2} , IOV_{DD1} , IOV_{DD2} , AV_{DD} , and LOV_{DD1} pins directly to the specified power supply and use at the same voltage.
 4. DRV_{DD1} , DRV_{DD2} , IOV_{DD1} , IOV_{DD2} , AV_{DD} , and LOV_{DD1} should be powered up at the same time.
 5. This IC has a built-in regulator, and makes the power supply voltage of DV_{DD} (Digital system supply voltage) inside the IC. Connect each of the DV_{DD1} , DV_{DD2} , and DV_{DD3} pins directly, and don't supply power to the DV_{DD1} , DV_{DD2} , and DV_{DD3} pins.
 6. The built-in regulator is only for this IC's DV_{DD} power. Do not use for power supply for any other devices. Also do not apply any external voltage to each of DV_{DD1} , DV_{DD2} , and DV_{DD3} pins.
 7. Connect a bypass capacitor of 10 μF between each of IOV_{DD2} and DV_{DD2} pins and DV_{SS} , and connect a bypass capacitor of 0.1 μF or larger between each of the power supply pins and ground.

■ Operating Supply Voltage Range $DV_{SS1,2,3}$, AV_{SS} , $LOV_{SS1} = 0\text{ V}$, $T_a = -30\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$

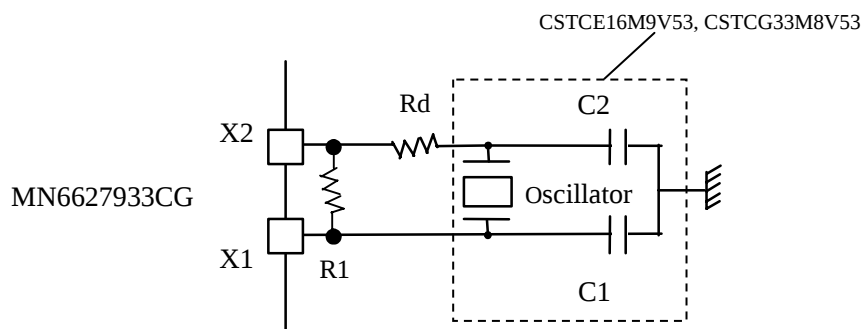
Parameter	Symbol	Conditions	Limits			Unit
			Min	Typ	Max	
B1	I/O system supply voltage	$IOV_{DD1,2}$	2.2	3.3	3.6	V
B2	Analog system supply voltage	AV_{DD}	2.4	3.3	3.6	V
B3	Audio system supply voltage	LOV_{DD1}	2.4	3.3	3.6	V
B4	D-RAM interface voltage	$DRV_{DD1,2}$	2.2	3.3	3.6	V

■ Operating Supply Voltage Range (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Self - excited Oscillation 1 * ¹							
B5	Oscillator frequency	fxtal	16.9344 MHz Oscillator * ²		16.9344		MHz
B6	Recommended external capacitance 1	C1			15		pF
B7	Recommended external capacitance 2	C2			15		
B8	Recommended external feedback resistance	R1			1		MΩ
B9		Rd			470		Ω
Self - excited Oscillation 2 * ¹							
B10	Oscillator frequency	fxtal	33.8688 MHz Oscillator * ³		33.8688		MHz
B11	Recommended external capacitance 1	C1			15		pF
B12	Recommended external capacitance 2	C2			15		
B13	Recommended external feedback resistance	R1			1		MΩ
B14		Rd			100		Ω

Note) *1: Oscillation circuit



*2: Values for C1 and C2 specified above are standard values when use CSTCE16M9V53 made in Murata Manufacturing Co., Ltd. as an oscillator. However, CSTCE16M9V53 builds in C1 and C2 of the above standard value.

The appropriate capacitors' values differ according to the oscillator used. Use the values specified by the oscillator manufacturer.

*3: Values for C1 and C2 specified above are standard values when use CSTCG33M8V53 made in Murata Manufacturing Co., Ltd. as an oscillator. However, CSTCG33M8V53 builds in C1 and C2 of the above standard value.

The appropriate capacitors' values differ according to the oscillator used. Use the values specified by the oscillator manufacturer.

■ Electrical Characteristics

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

1. DC Characteristics

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
C1	Supply current	I_{DD}	Anti-shock memory function used. No external load connected.		22	68	mA
C2	Total power consumption	P_T	(in 2× speed playback mode) ADPCM compression : ON MP3 decode : OFF CD-ROM decode : OFF Digital PLL : OFF		82.5	224.4	mW
C3	Supply current	I_{DD}	Anti-shock memory function used. No external load connected.		28	70	mA
C4	Total power consumption	P_T	(in 4× speed playback mode) MP3 decode : ON CD-ROM decode : ON Digital PLL : OFF		92.4	231	mW
C5	Supply current	I_{DD}	Anti-shock memory function used. No external load connected.		34	90	mA
C6	Total power consumption	P_T	(in 8× speed playback mode) MP3 decode : OFF CD-ROM decode : OFF Digital PLL : OFF		112.2	297	mW

■ Electrical Characteristics (continued)

$DRV_{DD1,2}$, $IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

1. DC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Input Pins 1 DRV_{DD} voltage type D0, D1, D2, D3, D4, D5, D6, D7, D8, D9, D10, D11, D12, D13, D14, D15							
C7	High-level input voltage	V_{IH1}		2.31		3.30	V
C8	Low-level input voltage	V_{IL1}		0.0		0.99	V
C9	Input leakage current	I_{LK1}	$V_{IN} = 0\text{ V or }3.3\text{ V}$			± 1	μA
Input Pins 2 IOV_{DD} voltage type EXT0, EXT1, EXT2, MCLK, MDATA, MLD, NRST							
C10	High-level input voltage	V_{IH2}		2.31		3.30	V
C11	Low-level input voltage	V_{IL2}		0.0		0.99	V
C12	Input leakage current	I_{LK2}	$V_{IN} = 0\text{ V or }3.3\text{ V}$			± 1	μA
Input Pins 3 AV_{DD} voltage type NRFDET, OFT , BDO, PWMSEL							
C13	High-level input voltage	V_{IH3}		2.31		3.30	V
C14	Low-level input voltage	V_{IL3}		0.0		0.99	V
C15	Input leakage current	I_{LK3}	$V_{IN} = 0\text{ V or }3.3\text{ V}$			± 1	μA
Input Pins NTEST							
C16	High-level input voltage	V_{IH4}		2.31		3.30	V
C17	Low-level input voltage	V_{IL4}		0.0		0.99	V
C18	Input leakage current	I_{LK4}	$V_{IN} = 0\text{ V or }3.3\text{ V}$			± 10	μA

■ Electrical Characteristics (continued)

$DRV_{DD1,2}$, $IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

1. DC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Output Pins 1 DRV_{DD} voltage type D0, D1, D2, D3, D4, D5, D6, D7, D8, D9, D10, D11, D12, D13, D14, D15, A0, A1, A2, A3, A4, A5, A6, A7, A8, A9, A10, A11, UDQM, LDQM, SDRCK, NWE, NCAS, NRAS, NCS							
C19	High-level output voltage	V_{OH1}	$I_{OH1} = -1.0\text{ mA}$	2.7			V
C20	Low-level output voltage	V_{OL1}	$I_{OL1} = 1.0\text{ mA}$			0.4	V
Output Pins 2 DRV_{DD} voltage type BA0, BA1							
C21	High-level output voltage	V_{OH2}	$I_{OH2} = -1.0\text{ mA}$	2.7			V
C22	Low-level output voltage	V_{OL2}	$I_{OL2} = 1.0\text{ mA}$			0.4	V
C23	Output leakage current	O_{LK2}	Hi-Z state $V_O = 0\text{ V}$ or 3.3 V			± 1	μA
Output Pins 3 IOV_{DD} voltage type SPPOL, TRVM, TRM, FOM, STAT, TX							
C24	High-level output voltage	V_{OH3}	$I_{OH3} = -1.0\text{ mA}$	2.7			V
C25	Low-level output voltage	V_{OL3}	$I_{OL3} = 1.0\text{ mA}$			0.4	V
Output Pin 4 IOV_{DD} voltage type SPOUT, TRVP, TRVP2, TRVM2, TRP, FOP, TMON1, TMON2, EXT0, EXT1, EXT2, BLKCK, SMCK, PMCK, FLAG							
C26	High-level output voltage	V_{OH4}	$I_{OH4} = -1.0\text{ mA}$	2.7			V
C27	Low-level output voltage	V_{OL4}	$I_{OL4} = 1.0\text{ mA}$			0.4	V
C28	Output leakage current	O_{LK4}	Hi-Z state $V_O = 0\text{ V}$ or 3.3 V			± 1	μA
Output Pins 5 AV_{DD} voltage type LDON							
C29	High-level output voltage	V_{OH5}	$I_{OH5} = -1.0\text{ mA}$	2.7			V
C30	Low-level output voltage	V_{OL5}	$I_{OL5} = 1.0\text{ mA}$			0.4	V
C31	Output leakage current	O_{LK5}	Hi-Z state $V_O = 0\text{ V}$ or 3.3 V			± 1	μA

■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

1. DC Characteristics (continued)

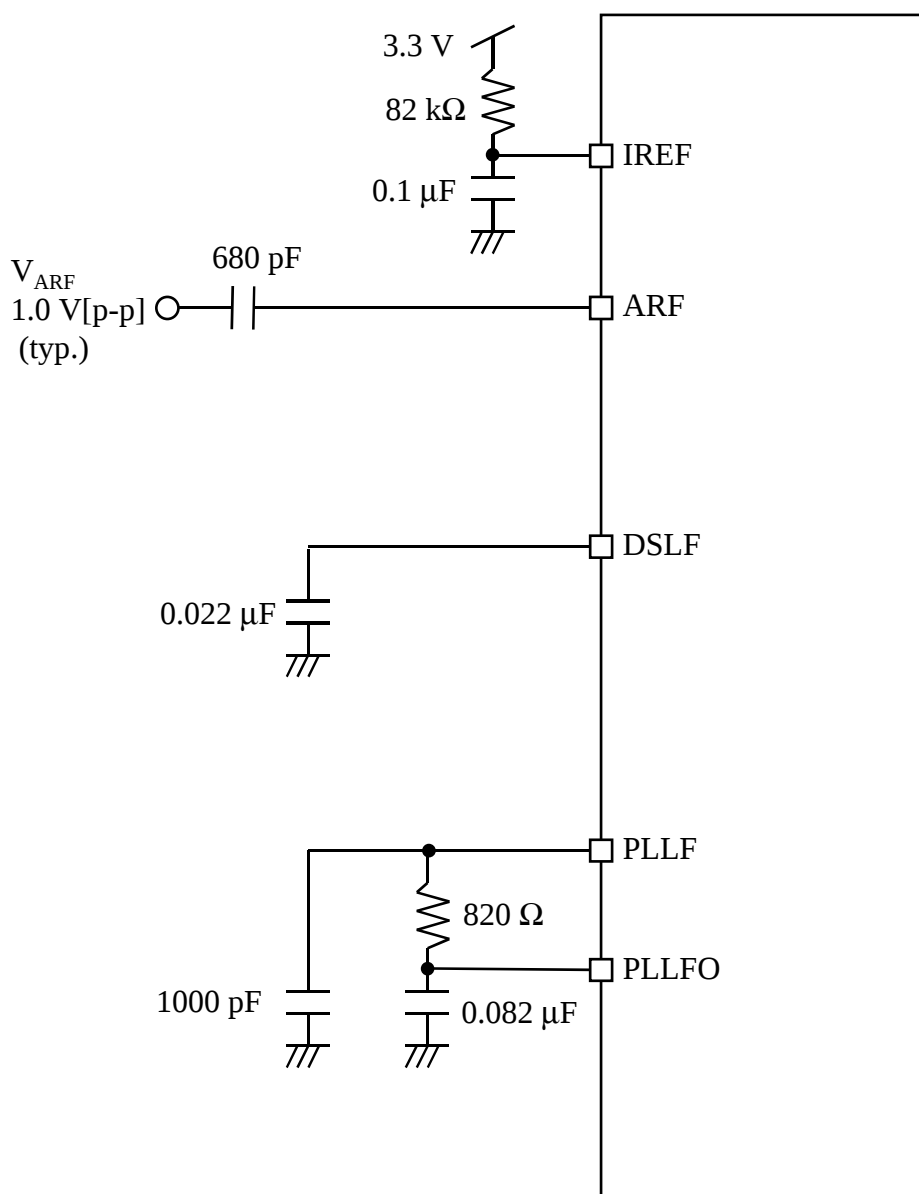
Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Analog System Input Pin 1 I_{REF}							
C32	Input current	I_{REF}	When pulled up with an 82 k Ω resistor.	18	29	41	μ A
Analog System Input Pin 2 ARF							
C33	nput signal amplitude	V_{ARF}	EFM signal input level in an application circuit of DSL block.	0.5	1.0		V[p-p]
C34	Internal resistance between ARF and DSLF pins	R_{ARF}	REGSEL: R1 + R2 + R3 setting	65	100	135	k Ω
			REGSEL: R2 + R3 setting	26	40	54	
			REGSEL: R3 setting	13	20	27	
			REGSEL: R1 + R2 + R3 and RFSW = ON setting	32	50	68	
Analog System Input Pin 3 TE, FE, RFENV, ADPV _{CC}							
C35	High-level input voltage	V_{IH4}				2.97	V
C36	Low-level input voltage	V_{IL4}		0.33			V
A/D Converter (for servo)							
C37	Resolution	RES				8	bit
C38	Integral nonlinearity	INL	A/D output = 99 to 66 (2's complement)			$\pm$ 2	LSB
C39	Differential nonlinearity	DNL				$\pm$ 3	LSB

■ Electrical Characteristics (continued)

$DRV_{DD1,2}$, $IOV_{DD1,2} = 3.3$ V, $DV_{SS1,2,3} = 0$ V, $AV_{DD} = 3.3$ V, $AV_{SS} = 0$ V, $LOV_{DD1} = 3.3$ V, $LOV_{SS1} = 0$ V

1. DC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Analog System Output Pin 1: DSLF (I _{REF} pin is pulled up to AV _{DD} with an 82 - kΩ resistor)							
C40	Output current (N)	I _{DSH}	BDO: Low, Tracking ON state DSLIF = 1.65 V	56	80	104	μA
C41	Output current (P)	I _{DSH}	BDO: Low, Tracking ON state DSLIF = 1.65 V	– 104	– 80	– 56	μA
C42	Output unbalance current	I _{DSEL}	BDO: Low, Tracking ON state Normal current mode	– 7	0	7	μA
Analog System Output Pin 2: PLLF (I _{REF} pin is pulled up to AV _{DD} with an 82 - kΩ resistor)							
C43	Phase comparator output current (N)	I _{PFH}	PLLF = 1.65 V	56	80	104	μA
C44	Phase comparator output current (P)	I _{PFH}	PLLF = 1.65 V	– 104	– 80	– 56	μA
C45	Input leakage current	I _{LKP}	Hi-Z state			± 1	μA
C46	Output unbalance current	I _{PLBL}	PLLF = 1.65 V	– 10	0	10	μA
C47	VCO oscillator frequency for PLL	f _{VCO1}		25.9		103.7	MHz
Analog System Output Pin 3: PLLFO (I _{REF} pin is pulled up to AV _{DD} with an 82 - kΩ resistor)							
C48	Output current (N)	I _{PFHO}		59	85	111	μA
C49	Output current (P)	I _{PFHO}		– 111	– 85	– 59	
C50	Input leakage current	I _{LKPO}	Hi-Z state			± 1	μA
Analog System Output Pin 4: TBAL, FBAL (I _{REF} pin is pulled up to AV _{DD} with an 82 - kΩ resistor)							
C51	Output current (N)	I _{BAH}	At default setting (× 1)	15	22	29	μA
C52	Output current (P)	I _{BAL}	At default setting (× 1)	– 29	– 22	– 15	μA

$DRV_{DD1,2} = 3.3\text{ V}, IOV_{DD1,2} = 3.3\text{ V}, DV_{SS1,2,3} = 0\text{ V}$
 $AV_{DD} = 3.3\text{ V}, AV_{SS} = 0\text{ V}$
 $LOV_{DD1} = 3.3\text{ V}, LOV_{SS1} = 0\text{ V}$


Recommended Circuit for DSL and PLL Blocks

Note) The above is a basic circuit. Calculate the constants and other factors of the circuit in consideration of playability when making use of this circuit for actual applications.

■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

1. DC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
D/A Converter Analog Characteristics *1, 2							
C53	Signal - to - noise ratio	S/N	EIAJ	90	97		dB
C54	Dynamic range	D. R.	EIAJ	86	94		dB
C55	Total harmonic distortion ratio	THD + N	EIAJ		0.005	0.009	%
C56	Crosstalk		EIAJ	80	85		dB
C57	Output level 1		1 kHz F. S. *3	1.04	1.33	1.62	V[rms]
C58	Output level difference		Difference between OUTL and OUTR pins at output level 20 log (V _R / V _L)	− 0.99		+ 0.99	dB
C59	Output level 2		1 kHz F.S. *4	0.69	0.88	1.07	V[rms]

Note) *1: The analog characteristics show the measured values when inserting a 15 Ω resistor between LOV_{DD1} and power supply. The above typical values are only reference values and not guaranteed.

*2: With no anti-shock memory function used, the operation of the D/A converter will not be guaranteed in modes other than normal-speed playback.

*3: The output level 1 shows the measured value at the output pin of the application circuit below.

*4: The output level 2 shows a value at the output pin of the IC and is calculated by taking the measured value of output level 1, dividing it by the circuit gain.

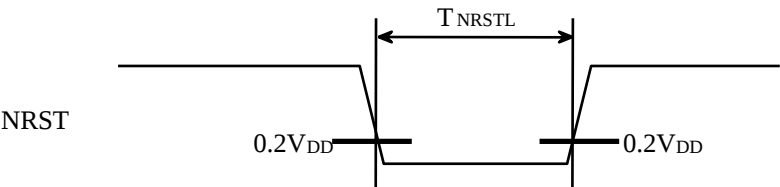
■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

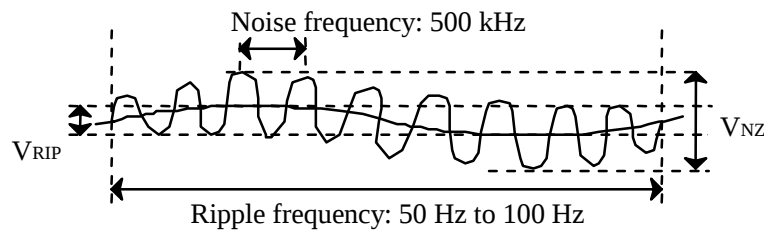
2. AC Characteristics

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Reset Timing *1							
C60	NRST pulse width	T _{NRSTL}		200			μs
Power Supply Ripple Noise *2							
C61	Ripple amplitude	V _{RIP}				15	mV[p-p]
C62	Ripple noise amplitude	V _{NZ}				30	mV[p-p]

Note) *1: When the power is turned on, reset with the NRST pulse which is equal to or exceeds the above pulse width only after the clock oscillation is stabilized within $\pm 10\%$ of error of the specified oscillator frequency. Keep noise on the reset line as low as possible.



Note) *2: The standard ripple noise values of the IC are guaranteed on condition that the values apply to typical 50-Hz to 100-Hz ripples with 500-kHz typical noise and that both the ripples and noise are in sine waveform as shown below.
The values, however, vary under the influence of other parts located on the PCB.
Therefore, be sure to apply the IC to practical applications and check the actual ripple noise values.



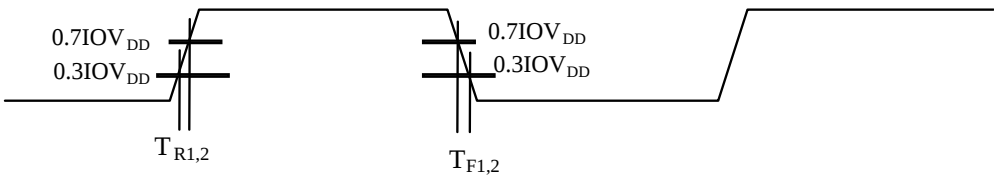
■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

2. AC Characteristics (continued)

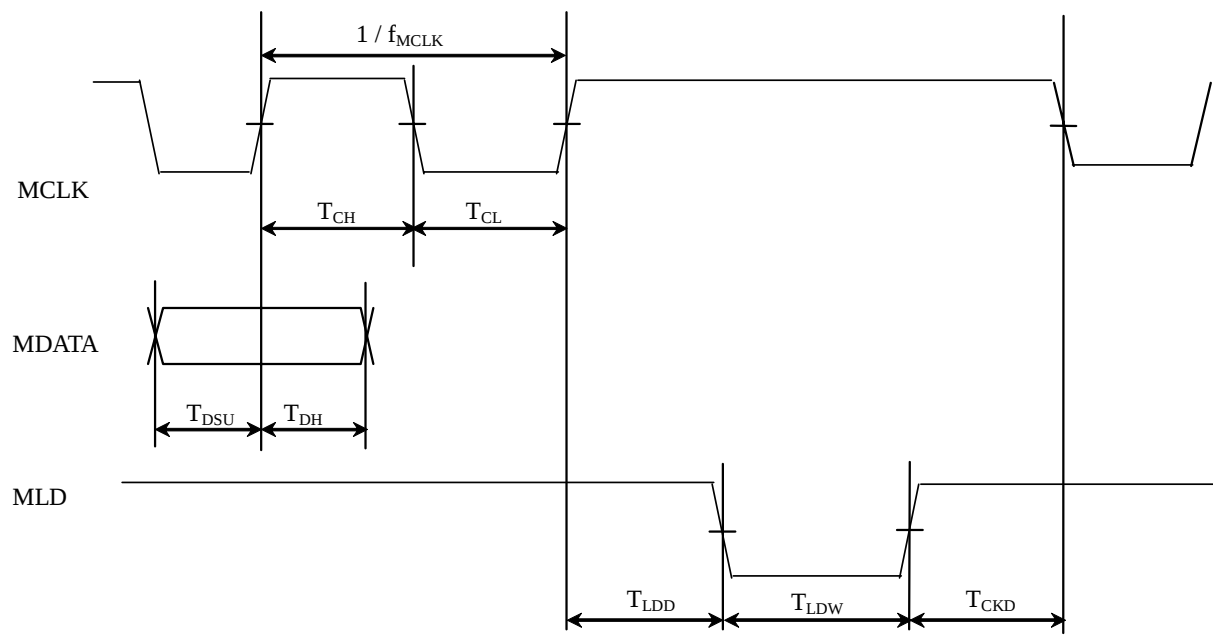
Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Transition Time 1 MCLK, MLD							
C63	Rise time	T _{R1}				250	ns
C64	Fall time	T _{F1}				250	ns
Transition Time 2 SBCK, TXTCK *							
C65	Rise time	T _{R2}				50	ns
C66	Fall time	T _{F2}				50	ns

Note) *: SBCK and TXTCK are input from EXT1.



■ Electrical Characteristics (continued)
 $DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$
2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Microcontroller Command Input Timing							
C67	Clock frequency	f _{MCLK}				2	MHz
C68	Clock pulse width	T _{CH,CL}		150			ns
C69	Data setup time	T _{DSU}		150			ns
C70	Data hold time	T _{DH}		150			ns
C71	MLD delay time	T _{LDD}		300			ns
C72	Latch pulse time	T _{LDW}		0.5		10	μs
C73	MCLK delay time	T _{CKD}		300			ns

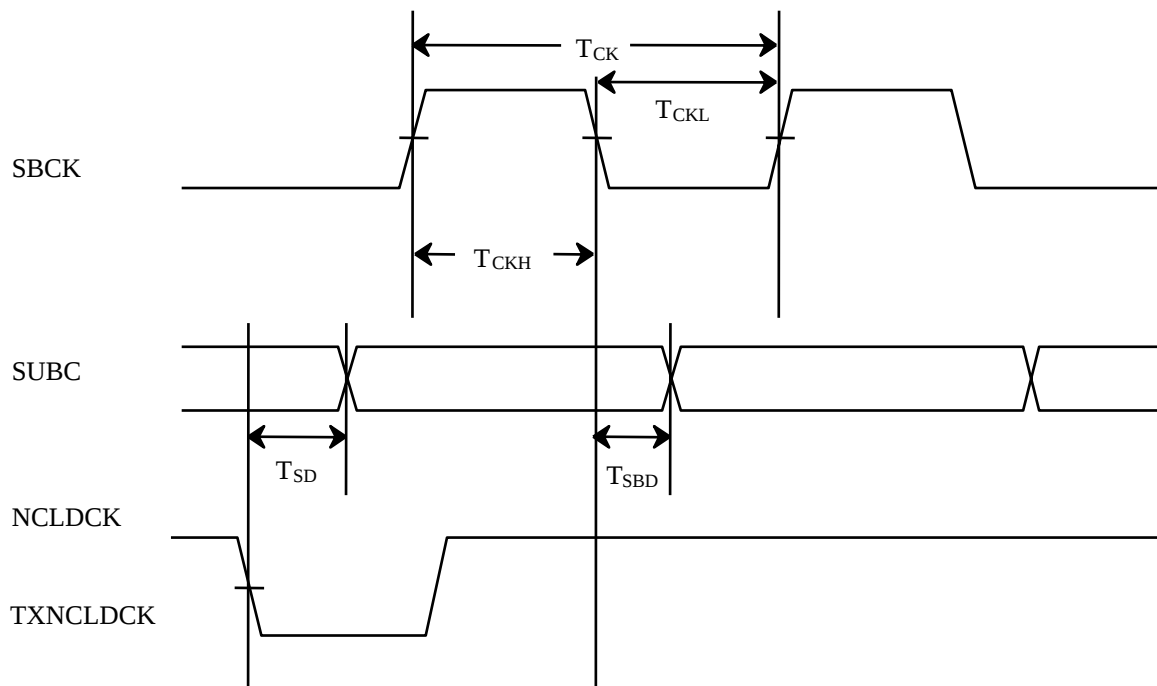


■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Subcode Interface SBCK, SUBC, TXNCLDCK * ¹							
C74	Clock width	T _{CK}		909			ns
C75	High-level pulse width	T _{CKH}		400			ns
C76	Low-level pulse width	T _{CKL}		400			ns
C77	Delay time	T _{SBD}	When digital filter is used. * ²			350	ns
			When no filter is used. * ²			173	ns
C78	Setup delay time	T _{SD}				150	ns



Note) *1: SBCK is output from EXT1, SUBC is output from EXT0, and TXNCLDCK is output from EXT2.

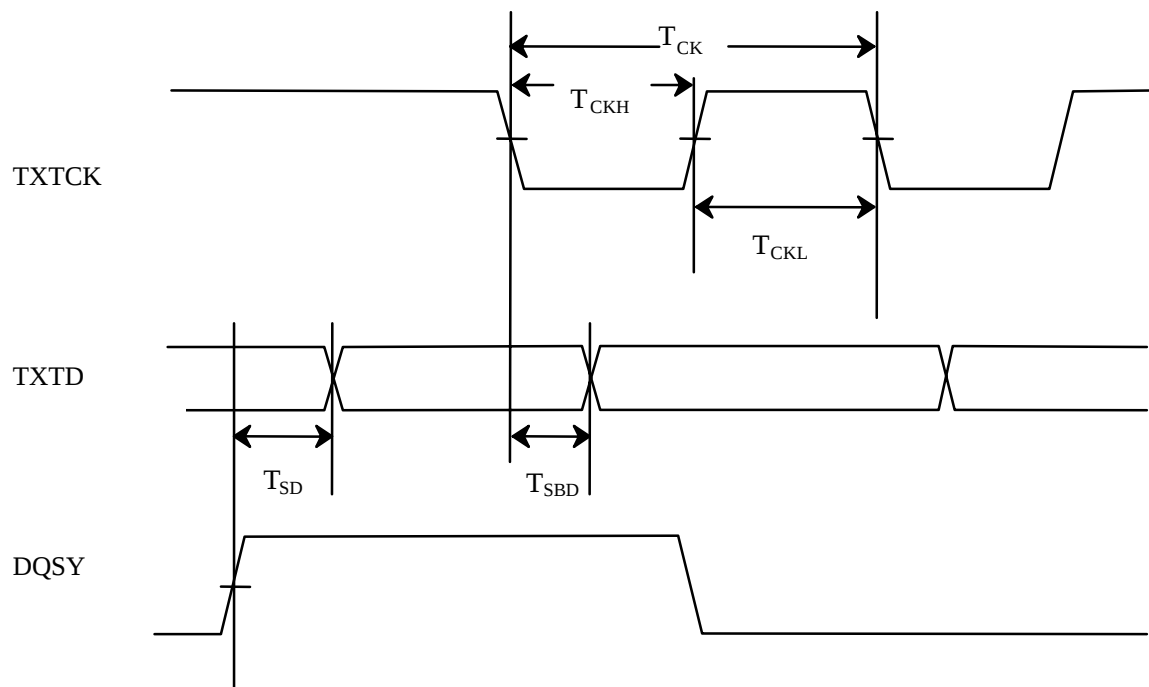
*2: SBCK, TXNCLDCK noise filter command is SBCKNF (by setting the D5 and D4 bits of the 67 command).

■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
Subcode Interface TXTCK, TXTD, DQSY *							
C79	Clock frequency	T _{CK}		2500			ns
C80	High-level pulse width	T _{CKH}		1200			ns
C81	Low-level pulse width	T _{CKL}		1200			ns
C82	Delay time	T _{SBD}				1150	ns
C83	Setup delay time	T _{SD}				1100	ns



Note) 1. *: TXTCK is input or output from EXT1, TXTD is output from EXT0, and TXNCLDCK is output from EXT2.

2. The cycle width of the readout clock TXTCK is proportional to disc rotation speed.

High-speed readout such as high-speed CLV playback or high-speed jitter-free playback using MSON (Memory system setting) is possible.

Example) When in 2x speed mode

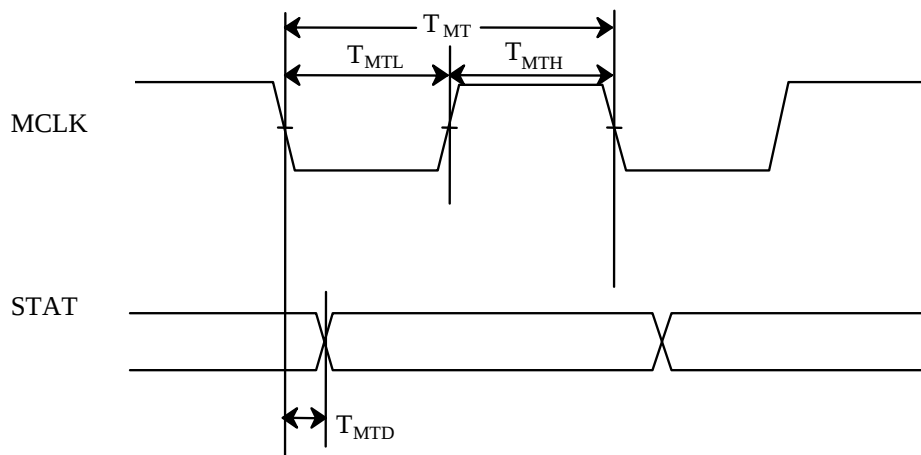
$T_{SBD2} = 450\text{ ns}$ (Typ.)

■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
STAT Output Interface (When analog filter 1 is used.) *1, 2							
C84	Clock width	T _{MT}		909			ns
C85	High-level pulse width	T _{MTH}		300			ns
C86	Low-level pulse width	T _{MTL}		300			ns
C87	Delay time	T _{MTD}				225	ns
STAT Output Interface (When analog filter 2 is used.) *1, 2							
C88	Clock width	T _{MT}		500			ns
C89	High-level pulse width	T _{MTH}		220			ns
C90	Low-level pulse width	T _{MTL}		220			ns
C91	Delay time	T _{MTD}				200	ns
STAT Output Interface (When no noise filter is used.) *1, 2							
C92	Clock width	T _{MT}		500			ns
C93	High-level pulse width	T _{MTH}		220			ns
C94	Low-level pulse width	T _{MTL}		220			ns
C95	Delay time	T _{MTD}				173	ns



Note) *1: In multiple-byte read mode using REGRD command (96h), VWA_ID command (97h), or VWAIDRD command (98h), it is necessary to set the high-level pulse width T_{MTH} to more than 450 ns in 1-byte increments.

*2: MCLK,MDATA,MLD noise filter command is MCIFNF (by setting the D5 and D4 bits of the 67 command).

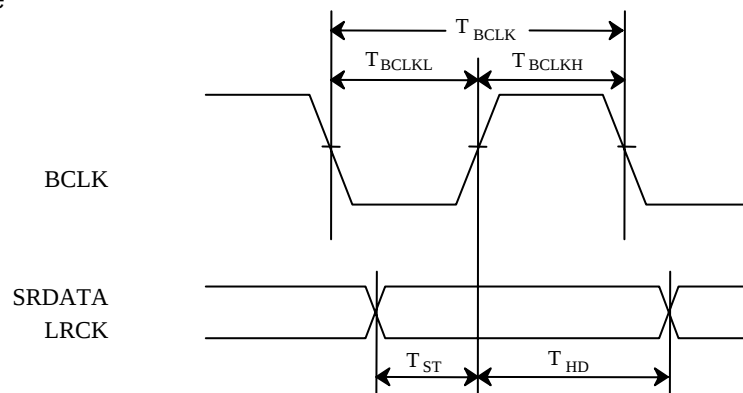
■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
D/A Output Interface 1							
C96	Clock width	T _{BCLK}	In normal-speed playback mode (64fs)		354		ns
C97	High-level pulse width	T _{BCLKH}			177		ns
C98	Low-level pulse width	T _{BCLKL}			177		ns
C99	Setup time	T _{ST}		70			ns
C100	Hold time	T _{HD}		70			ns
D/A Output Interface 2							
C101	Clock width	T _{BCLK}	In 4× speed playback mode (48fs)		118		ns
C102	High-level pulse width	T _{BCLKH}			59		ns
C103	Low-level pulse width	T _{BCLKL}			59		ns
C104	Setup time	T _{ST}		30			ns
C105	Hold time	T _{HD}		30			ns
D/A Output Interface 3							
C106	Clock width	T _{BCLK}	In 8× speed playback mode (48fs)		59		ns
C107	High-level pulse width	T _{BCLKH}			29.5		ns
C108	Low-level pulse width	T _{BCLKL}			29.5		ns
C109	Setup time	T _{ST}		15			ns
C110	Hold time	T _{HD}		15			ns

D/A Output Interface



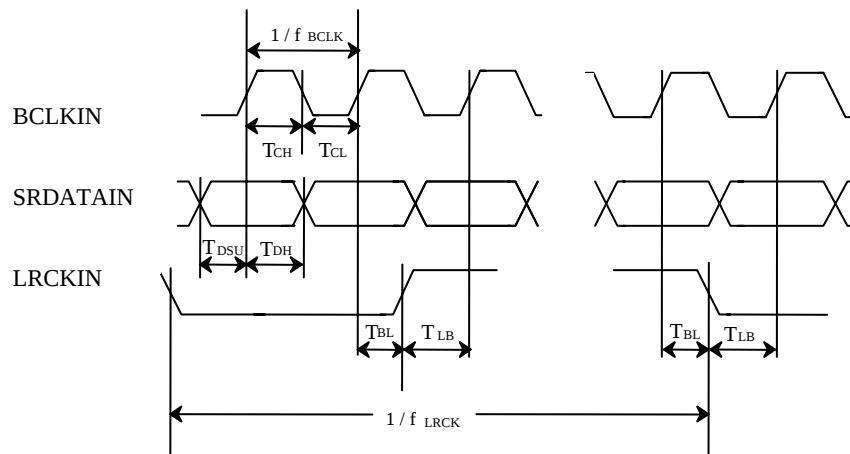
Note) SRDATA, BCLK, and LRCK are output in combination with PMCK (BCLK), FLAG (SRDATA), and SMCK (LRCK) or EXT0 (SRDATA), EXT1 (LRCK), and EXT2 (BCLK).

■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
D/A Converter Input Timing 1 (When no noise filter is used.) *1, 2							
C111	BCLK frequency	f _{BCLK}			2.8		ns
C112	SCLK pulse width	T _{CH,CL}		100			ns
C113	Data setup time	T _{DSU}		100			ns
C114	Data hold time	T _{DH}		100			ns
C115	LRCK frequency	f _{LRCK}			44.1		kHz
C116	BCLK-LRCK timing	T _{BL} , T _{LB}		100			ns
D/A Converter Input Timing 2 (When digital filter is used.) *1, 2							
C117	BCLK frequency	f _{BCLK}			2.8		ns
C118	SCLK pulse width	T _{CH,CL}		150			ns
C119	Data setup time	T _{DSU}		100			ns
C120	Data hold time	T _{DH}		100			ns
C121	LRCK frequency	f _{LRCK}			44.1		kHz
C122	BCLK-LRCK timing	T _{BL} , T _{LB}		100			ns



Note) *1: SRDATAIN, BCLK, LRCK noise filter command is SRDATANF (by setting the D7 and D6 bits of the 67 command).

*2: SRDATAIN, LRCKIN, and BCLKIN are input from EXT0 (SRDATAIN), EXT1 (LRCKIN), and EXT2 (BCLKIN) respectively.

■ Electrical Characteristics (continued)

 $\text{DRV}_{\text{DD1},2}, \text{IOV}_{\text{DD1},2} = 3.3 \text{ V}, \text{DV}_{\text{SS1},2,3} = 0 \text{ V}, \text{AV}_{\text{DD}} = 3.3 \text{ V}, \text{AV}_{\text{SS}} = 0 \text{ V}, \text{LOV}_{\text{DD1}} = 3.3 \text{ V}, \text{LOV}_{\text{SS1}} = 0 \text{ V}$

1. AC Characteristics (continued) (In BCKSEL = 0 mode)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
EDO, First-Page DRAM Interface Read / Write Cycle							
C123	A0 to A11 row address setup time	t _{ASR}			2		cycle
C124	A0 to A11 row address hold time	t _{RAH}			1		cycle
C125	A0 to A11 column address setup time	t _{ASC}			1		cycle
C126	A0 to A11 column address hold time	t _{CAH}			2		cycle
C127	RAS-CAS delay time (NCAS0, NCAS1)	t _{RCD}			2		cycle
C128	RAS access time	t _{RAC}			4		cycle
C129	CAS access time	t _{CAC}			2		cycle
C130	Write enable signal NWE setup time	t _{WCS}			2		cycle
C131	Write enable signal NWE hold time	t _{WCH}			2		cycle
C132	D0 to D15 write data setup time	t _{DWDS}			1		cycle
C133	D0 to D15 write data hold time	t _{DWDH}			2		cycle
EDO, First-Page DRAM Interface Page Mode Data Transfer							
C134	CAS pre-charge pulse width	t _{CP}			1		cycle
C135	CAS low-level pulse width	t _{CAS}			2		cycle
C136	RAS hold time	t _{RSH}			2		cycle
EDO, First-Page DRAM Interface CAS Before RAS Refresh							
C137	CAS-RAS delay time	t _{CRD}			1		cycle
C138	Refresh RAS low-level pulse width	t _{RRAS}			4		cycle
C139	Refresh CAS low-level pulse width	t _{RCAS}			5		cycle

Note) One cycle is the system clock cycle of 1 / (16.9344 MHz or 33.8688 MHz) [s].

The system clock frequencies, 16.9344 MHz and 33.8688 MHz, are determined according to the DCKSEL command (65h command D6 and D5).

■ Electrical Characteristics (continued)

$DRV_{DD1,2}$, $IOV_{DD1,2}$ = 3.3 V, $DV_{SS1,2,3}$ = 0 V, AV_{DD} = 3.3 V, AV_{SS} = 0 V, LOV_{DD1} = 3.3 V, LOV_{SS1} = 0 V

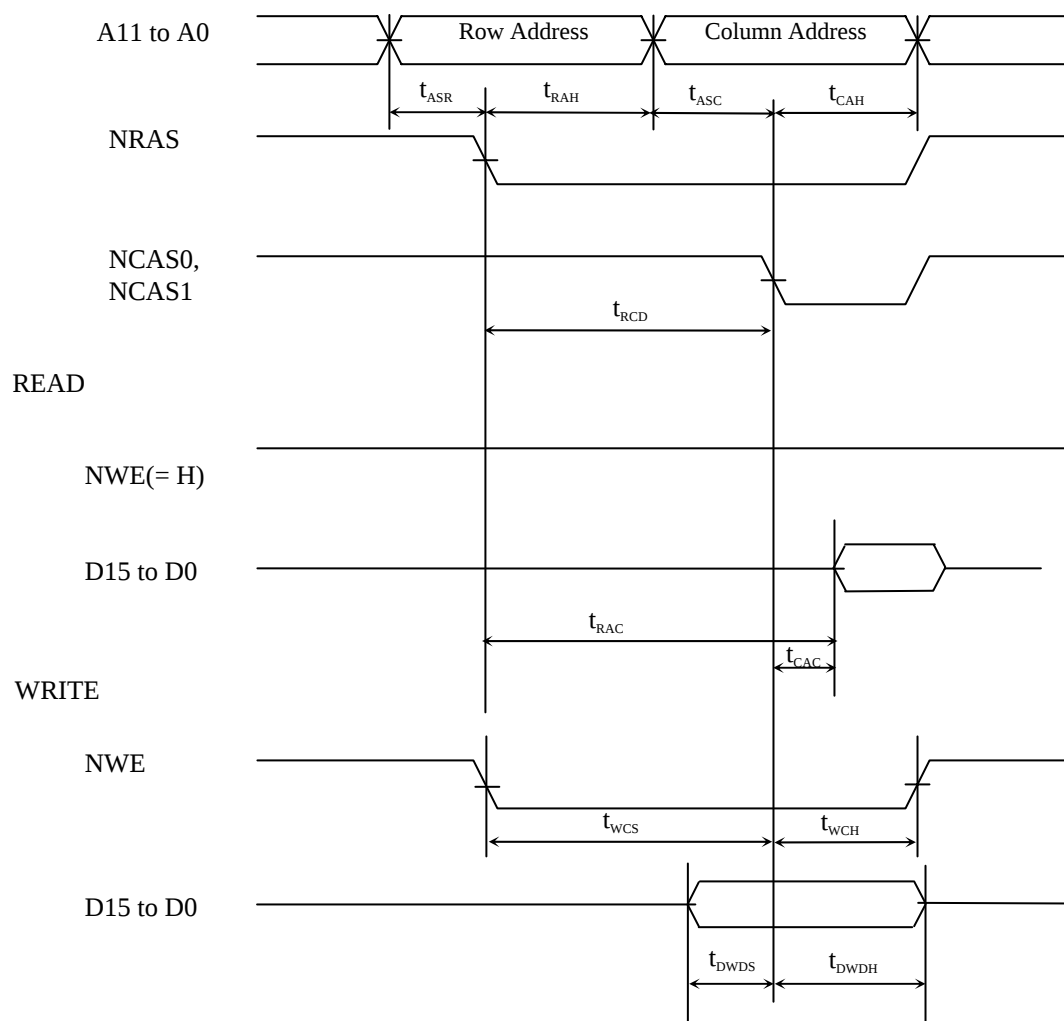
2. AC Characteristics (continued) (In BCKSEL = 1 mode)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
EDO, First-Page DRAM Interface Read / Write Cycle							
C140	A0 to A11 row address setup time	t _{ASR}			2		cycle
C141	A0 to A11 row address hold time	t _{RAH}			1		cycle
C142	A0 to A11 column address setup time	t _{ASC}			1		cycle
C143	A0 to A11 column address hold time	t _{CAH}			1		cycle
C144	RAS-CAS delay time (NCAS0, NCAS1)	t _{RCD}			2		cycle
C145	RAS access time	t _{RAC}			4		cycle
C146	CAS access time	t _{CAC}			1		cycle
C147	Write enable signal NWE setup time	t _{WCS}			2		cycle
C148	Write enable signal NWE hold time	t _{WCH}			1		cycle
C149	D0 to D15 write data setup time	t _{DWDS}			1		cycle
C150	D0 to D15 write data hold time	t _{DWDH}			1		cycle
EDO, First-Page DRAM Interface Page Mode Data Transfer							
C151	CAS pre-charge pulse width	t _{CP}			1		cycle
C152	CAS low-level pulse width	t _{CAS}			1		cycle
C153	RAS hold time	t _{RSH}			1		cycle
EDO, First-Page DRAM Interface CAS Before RAS Refresh							
C154	CAS-RAS delay time	t _{CRD}			1		cycle
C155	Refresh RAS low-level pulse width	t _{RRAS}			4		cycle
C156	Refresh CAS low-level pulse width	t _{RCAS}			5		cycle

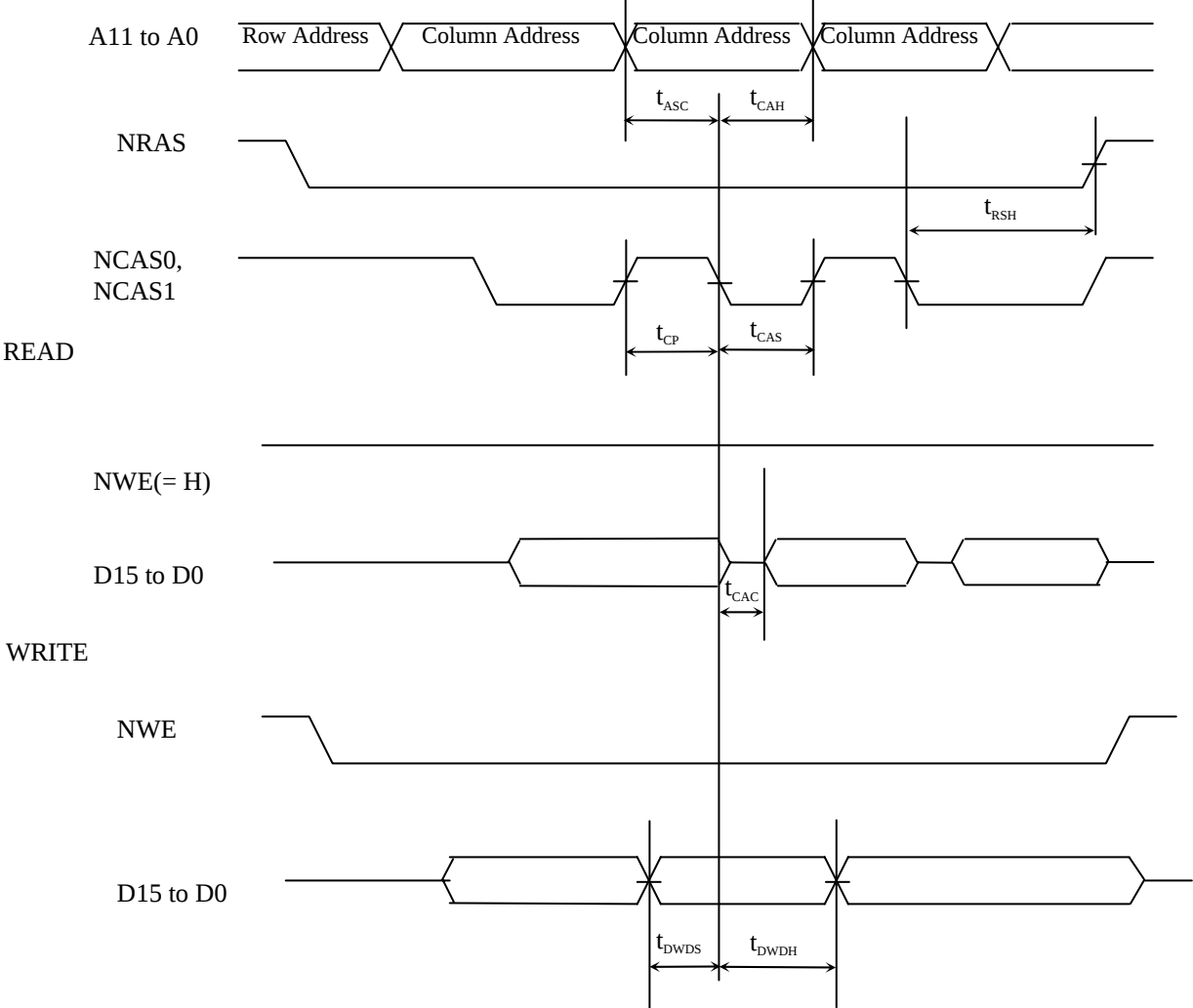
Note) One cycle is the system clock cycle of 1 / (16.9344 MHz or 33.8688 MHz) [s].

The system clock frequencies, 16.9344 MHz and 33.8688 MHz, are determined according to the DCKSEL command (65h command D6 and D5).

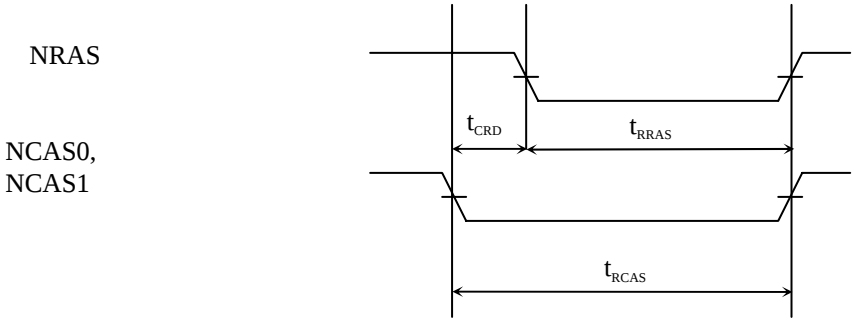
EDO, First-Page DRAM Access Timing (NRAS, NCAS0, NCAS1, NWE, A0 to A11, D0 to D15)
 < Normal mode >



< Page mode >



< CAS Before RAS Refresh Mode >



■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
SDRAM Interface							
C157	SDRCK cycle time	t _{CLK}			1		cycle
C158	SDRCK high-level pulse width	t _{CH}			0.5		cycle
C159	SDRCK low-level pulse width	t _{CL}			0.5		cycle
C160	NCS input setup time	t _{CSS}			0.5		cycle
C161	NCS input hold time	t _{CSH}			0.5		cycle
C162	NRAS input setup time	t _{RAS}			0.5		cycle
C163	NRAS input hold time	t _{RAH}			0.5		cycle
C164	NCAS input setup time	t _{CAS}			0.5		cycle
C165	NCAS input hold time	t _{CAH}			0.5		cycle
C166	New input setup time	t _{WES}			0.5		cycle
C167	New input hold time	t _{WEH}			0.5		cycle
C168	LDQM, UDQM input setup time	t _{DMS}			0.5		cycle
C169	LDQM, UDQM input hold time	t _{DMH}			0.5		cycle
C170	D0 to D15 input setup time	t _{DQS}			1		cycle
C171	D0 to D15 input hold time	t _{DQH}			1		cycle
C172	A0 to A11, BA0, BA1 input setup time	t _{AS}			1		cycle
C173	A0 to A11, BA0, BA1 input hold time	t _{AH}			1		cycle

Note) 1. One cycle is the system clock cycle of 1 / (16.9344 MHz or 33.8688 MHz) [s].

2. Connect SDRAM near this LSI as much as possible.

Connect the wiring load of the SDRCK pin specially within 5 pF.

■ Electrical Characteristics (continued)

$DRV_{DD1,2}, IOV_{DD1,2} = 3.3\text{ V}$, $DV_{SS1,2,3} = 0\text{ V}$, $AV_{DD} = 3.3\text{ V}$, $AV_{SS} = 0\text{ V}$, $LOV_{DD1} = 3.3\text{ V}$, $LOV_{SS1} = 0\text{ V}$

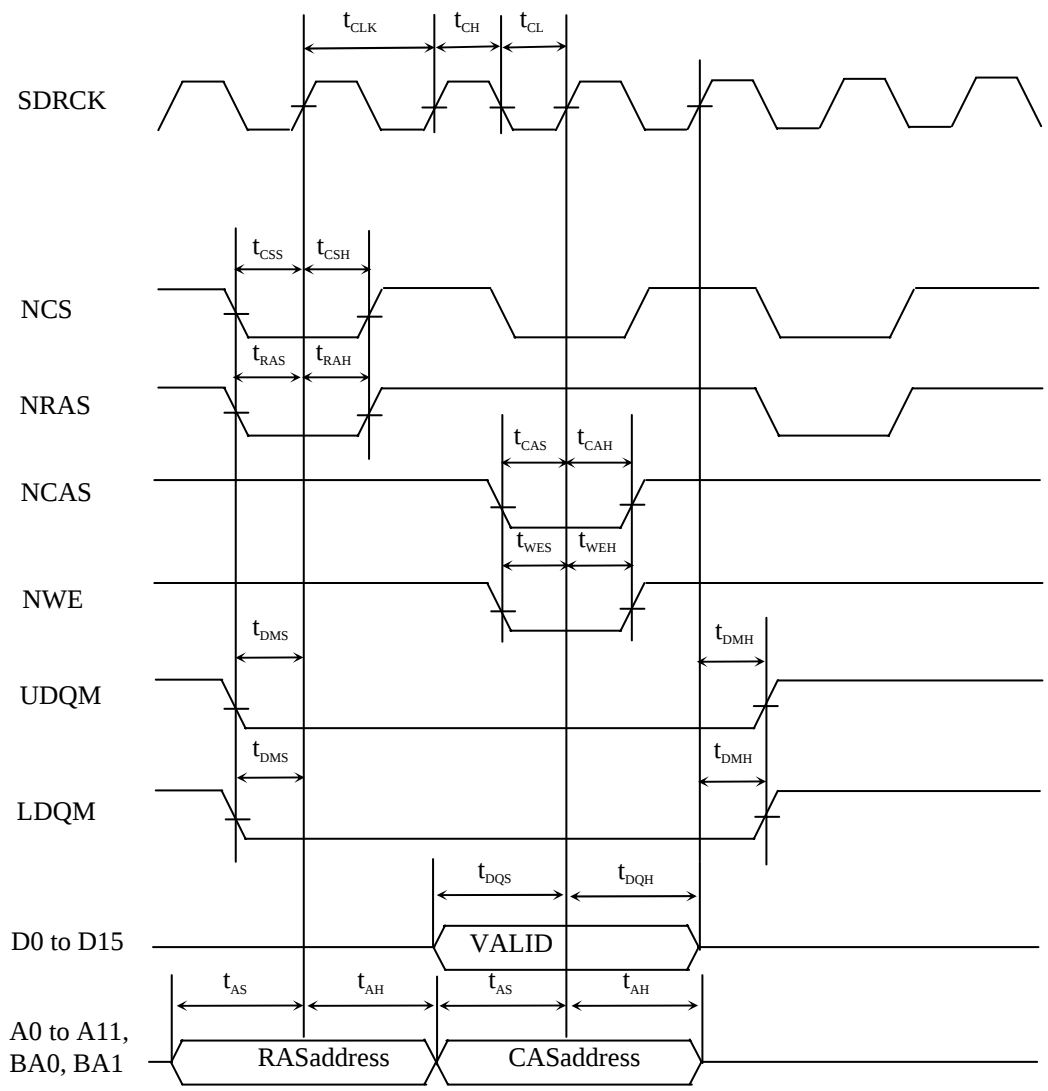
2. AC Characteristics (continued)

Parameter		Symbol	Conditions	Limits			Unit
				Min	Typ	Max	
SDRAM Interface							
C174	Access time from SDRCK	t _{AC}				15	ns
C175	Hi-Z output time from SDRCK	t _{OH}		0			ns
C176	Low impedance output time from SDRCK	t _{OLZ}		0			ns
C177	High impedance output time from SDRCK	t _{OHZ}		0			ns

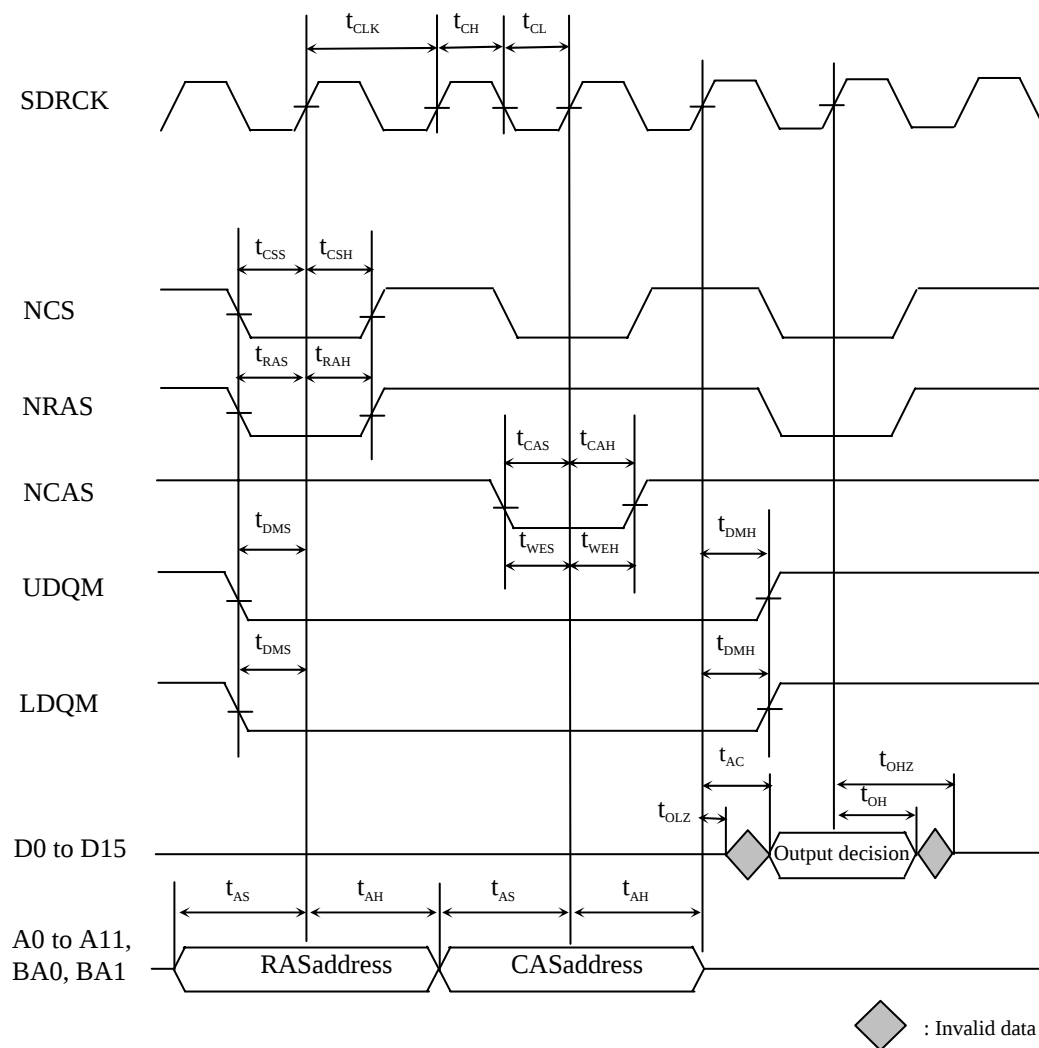
Note) One cycle is the system clock cycle of 1 / (16.9344 MHz or 33.8688 MHz) [s].

SDRAM Access Timing (SDRCK, NCS, NCAS, NWE, LDQM, UDQM, A0 to A11, BA0, BA1, D0 to D15)

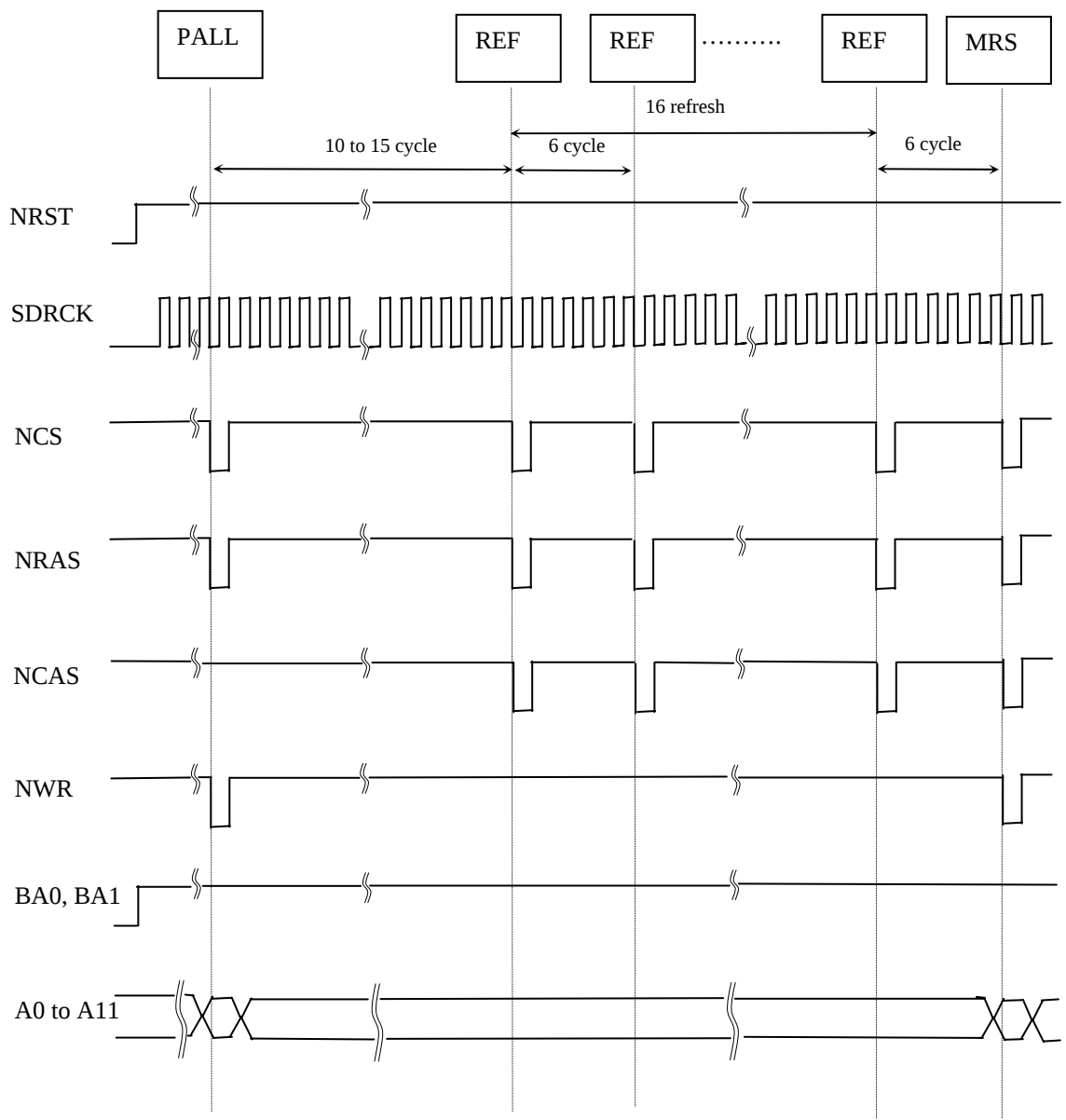
WRITE



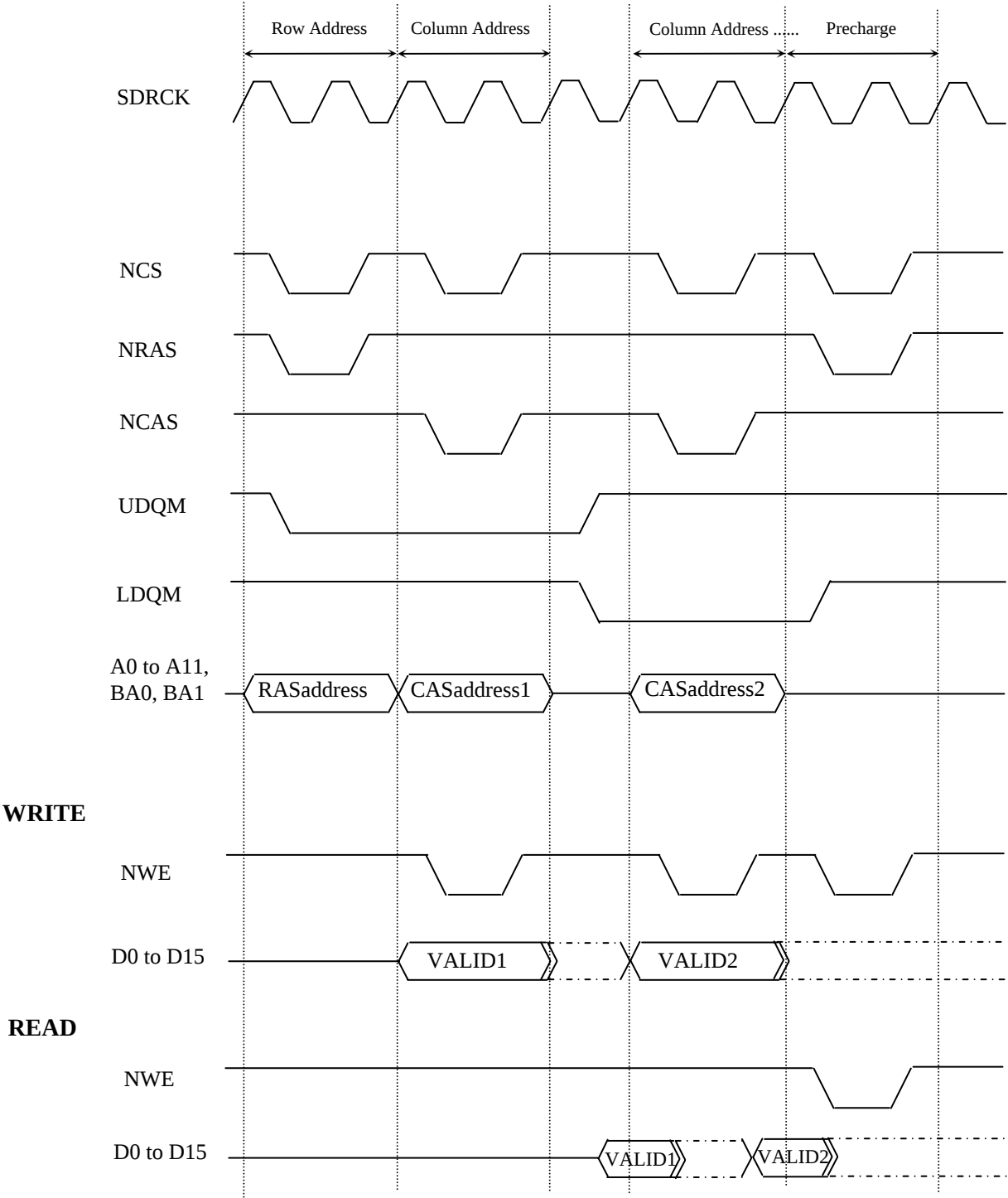
READ



SDRAM Initialize Sequence (SDRCK, NCS, NCAS, NWE, A0 to A11, BA0, BA1)



SDRAM Page Access Timing (SDRCK, NCS, NRAS, NCAS, NWE, A0 to A11, BA0, BA1)



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